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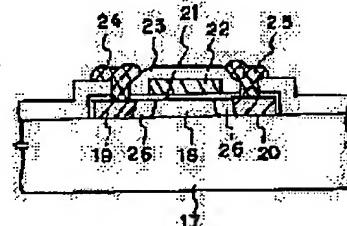
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(54) SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To reduce leakage current in an OFF state of a thin film transistor.

CONSTITUTION: In a semiconductor device having a thin film transistor formed on a substrate, a semiconductor device where the thin film transistor consists of a thin polycrystalline film semiconductor 18 and has a low-doped region 26 adjacent to at least either the source region 19 or the drain region 20 of the thin film transistor and equal to this region in conductivity.



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